EAST - [default.wsp 1]

File View Edit Tools Window Help

- Drafts
  - BRS: L6 and L10 and (
- Pending
- Active
  - L1: (2) (IGFET or Insulated near gate near filed near effec
  - L2: (3) (IGFET or Insulated near gate near filed near effec
  - L3: (11) (IGFET or Insulated near gate near field near effe
  - L4: (0) (IGFET or Insulated near gate near field near effec
  - L5: (0) (IGFET or Insulated near gate near field near effec
  - L6: (8683) (IGFET or Insulated near gate near field near ef
  - L7: (0) (IGFET or Insulated near gate near field near effec
  - L8: (0) (IGFET or Insulated near gate near field near effec
  - L9: (0) (gate near elctrode) and (multiple near layer)
  - L10: (769) (gate near electrode) and (multiple near layer
  - L11: (54) L6 and L10
  - L12: (3) L6 and L10 and (group near IV)
- Failed
  - (0) (IGFET or Insulated near gate near filed near effect ne
- Saved

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DBs: USPAT; EPO; JPO; DERWENT — Plurals — Synonyms

Default operator: OR — Highlight all hit terms initially

L6 and L10 and (group near IV)

BRS form | IS&R form | Image | Text

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRe	Retrieval	Inventor	S	C	P	2	3		
1	☐	☐	US 5254862 A	19931019	10	Diamond field-effect transistor with a particu	257/77	257/192 ; 257/412		Kalyankjumar, Das , et al.	☑	☐	☐	☐	☐	☐	☐
2	☐	☐	US 4839702 A	19890613	13	Semiconductor device based on charge emission	257/23			Grinberg, Anatoly , et al.	☑	☐	☐	☐	☐	☐	☐
3	☐	☐	US 4394749 A	19830719	13	Photoelectric device and method of producing the s	365/106	257/290 ; 365/112		Tsukada, Toshihisa , et al.	☑	☐	☐	☐	☐	☐	☐

Hits | Details

Ready — NUM